

**IN THE CLAIMS:**

Please cancel claims 1 and 2 without prejudice to or disclaimer of the subject matter therein.

Please add new claim 10.

Please amend claims 3-9 as follows:

3. (Amended) A semiconductor device comprising:

a substrate;

an insulating film of a fluorine-contained carbon film formed on said substrate, wherein the surface of said insulating film is irradiated with hydrogen plasma;

a wiring layer of copper formed on said insulating film; and

an adhesion layer formed between said insulating film and said wiring layer, for preventing said wiring layer from being peeled off from said insulating film, wherein said adhesion layer includes

a metal layer of a metal, and

a layer of a compound containing carbon and said metal.

4. (Amended) A semiconductor device as set forth in claim 2, wherein said

metal layer is formed of an element selected from the group consisting of titanium, molybdenum, chromium, cobalt, tantalum, niobium and zirconium.

5. (Amended) A semiconductor device as set forth in claim 3 or claim 4,

wherein said insulating film is amorphous.

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6. (Amended) A semiconductor device as set forth in claim 3 or claim 4, wherein said insulating film has a film density of  $1.5 \text{ g/cm}^3$  or higher.

7. (Amended) A semiconductor device as set forth in claim 3 or claim 4, wherein said insulating film contains oxygen having a concentration of 3 atomic% or less.

8. (Amended) A semiconductor device as set forth in claim 3 or claim 4, wherein said insulating film contains nitrogen having a concentration of 3 atomic% or less.

9. (Amended) A semiconductor device as set forth in claim 3 or claim 4, wherein said insulating film contains boron having a concentration of from  $10^{-3}$  atomic% to 1 atomic%.

10. (New) A semiconductor device as set forth in claim 3, wherein said metal layer is disposed adjacent said wiring layer, and said layer of a compound is disposed adjacent said insulating film.

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